

## Design Summary

IC: L6566B - SO 16-N

Input: 185 - 265 Vac ( 47 - 53 Hz ) - Nominal: 230 Vac

Output: 12 V (2 % ripple) - 36 W max

Switching Frequency: 30 kHz - 120 kHz

Expected Average Efficiency: 87 %

Max. Ambient Temperature: 60 °C

### Transformer Specifications:

fsw range: 30 kHz - 120 kHz - Lp: 2.92 mH - leakage: 29.24 µH

Primary - Ipk: 971 mA - Irms: 310 mA

Secondary - Irms: 4.28 A - Np/Ns: 11.719

Auxiliary - Irms: 29 mA - Iavg: 20 mA - Np/Naux: 11.719

### Transformer Design:

#### Core:

Type EER28 Vertical - Area Product 5895 mm<sup>4</sup> - Orientation Vertical

Volume (Ve) 5250 mm<sup>3</sup> - Cross-Sectional Area (Ae) 82.10 mm<sup>2</sup> - Bobbin Winding Area (Aw) 71.80 mm<sup>2</sup>

Bobbin Average Turn Length 52.20 mm - Bobbin Centr. Leg Length 16.70 mm

Material: N27, N67, N87, 3C81, 3C90, 3C91, 3C95, PC40, PC44, PC50 or equivalent

Core Gap: 0.48 mm

Inductance factor (AL): 214 nH/N<sup>2</sup>

Primary: Turns 117 - Layers 4

Wire: Type TIW - Number of strands 1 - Strand copper Ø 0.300 mm

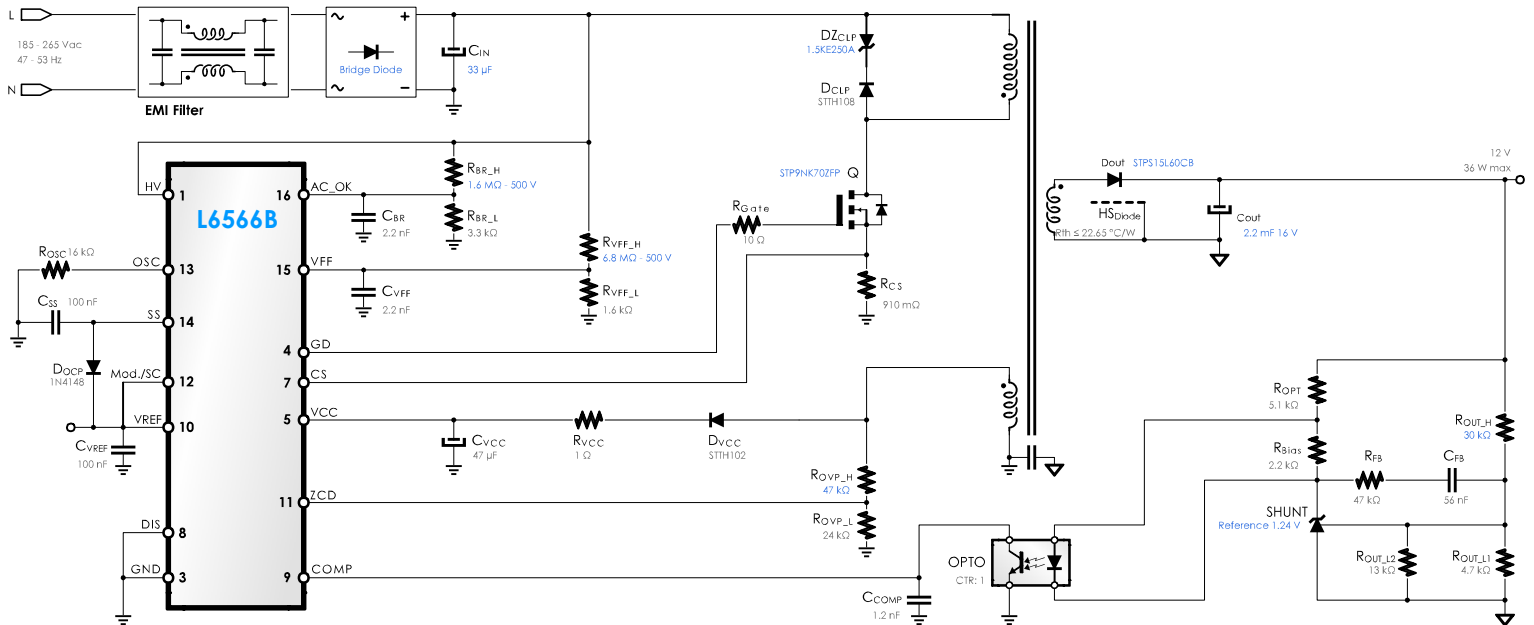
Wire gross Ø 0.500 mm - Resistance per meter 0.2629 Ω/m

Secondary: Turns 10 - Layers 2 - Paralleled wires 3

Wire: Type Litz - Number of strands 45 - Strand copper Ø 0.100 mm

Wire gross Ø 1.073 mm - Resistance per meter 0.0559 Ω/m

Auxiliary: Turns 10



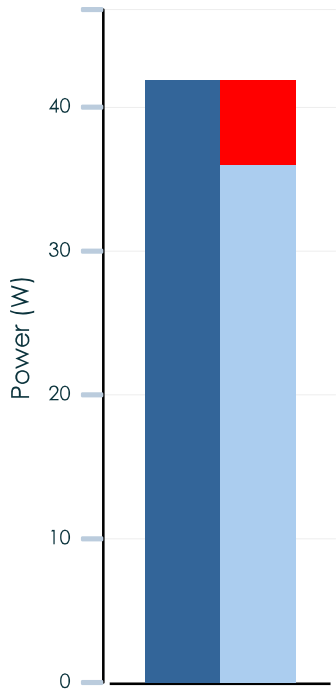
## Bill of Materials

Reference	Value	Description
IC	L6566B	PWM Controller
Q	STP9NK70ZFP	Power MOSFET
Rgate	10 $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
DZclp	1.5KE250A	250 V Transil
Dclp	STTH108	800 V Diode
Rosc	16 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Css	100 nF	50 V Standard ceramic capacitor
Rcs	910 m $\Omega$	1/4 W Resistor - 5% 250 ppm/ $^{\circ}$ C
Rbr_h	1.6 M $\Omega$ - 500 V	High Voltage Resistor - 1% 100 ppm/ $^{\circ}$ C
Rbr_l	3.3 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Cbr	2.2 nF	50 V Standard ceramic capacitor
Rovp_h	47 k $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
Rovp_l	24 k $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
Docp	1N4148	Fast signal diode
Rvff_h	6.8 M $\Omega$ - 500 V	High Voltage Resistor - 1% 100 ppm/ $^{\circ}$ C
Rvff_l	1.6 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Cvff	2.2 nF	50 V Standard ceramic capacitor
Cvref	100 nF	50 V Standard ceramic capacitor
Cvcc	47 $\mu$ F	35 V Electrolytic capacitor
Rvcc	1 $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
Dvcc	STTH102	High efficiency ultrafast diode
SHUNT	Reference 1.24 V	Shunt voltage reference
Rout_h	30 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Rout_l1	4.7 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Rout_l2	13 k $\Omega$	Standard Resistor - 1% 100 ppm/ $^{\circ}$ C
Cin	33 $\mu$ F	400 V Electrolytic capacitor
BD	Bridge Diode	600 V Bridge rectifier
Cout	2.2 mF 16 V	16 V - ESR $\leq$ 15 m $\Omega$ - Electrolytic capacitor
Dout	STPS15L60CB	Low drop power schottky rectifier
HSdiode	Rth $\leq$ 22.65 $^{\circ}$ C/W	Heatsink
Ccomp	1.2 nF	50 V Standard ceramic capacitor
Cfb	56 nF	50 V Standard ceramic capacitor
Rfb	47 k $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
Ropto	5.1 k $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C



Reference	Value	Description
Rbias	2.2 k $\Omega$	Standard Resistor - 5% 250 ppm/ $^{\circ}$ C
OPTO	CTR: 1	Optocoupler - CTR: 1

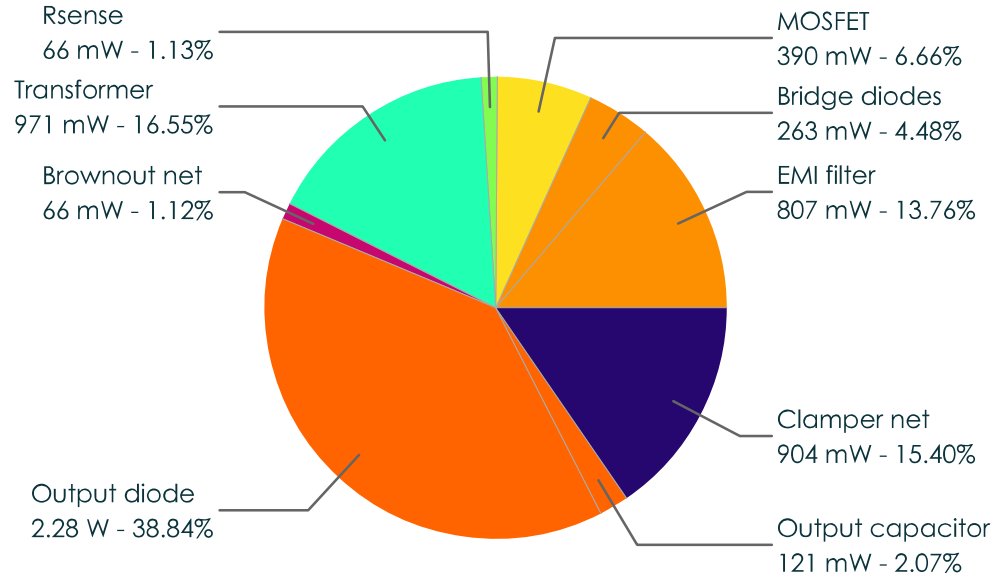
## Power Losses @ ( Vin 230 Vac - Pout 36 W )



Pin: 41.89 W Pout: 36 W

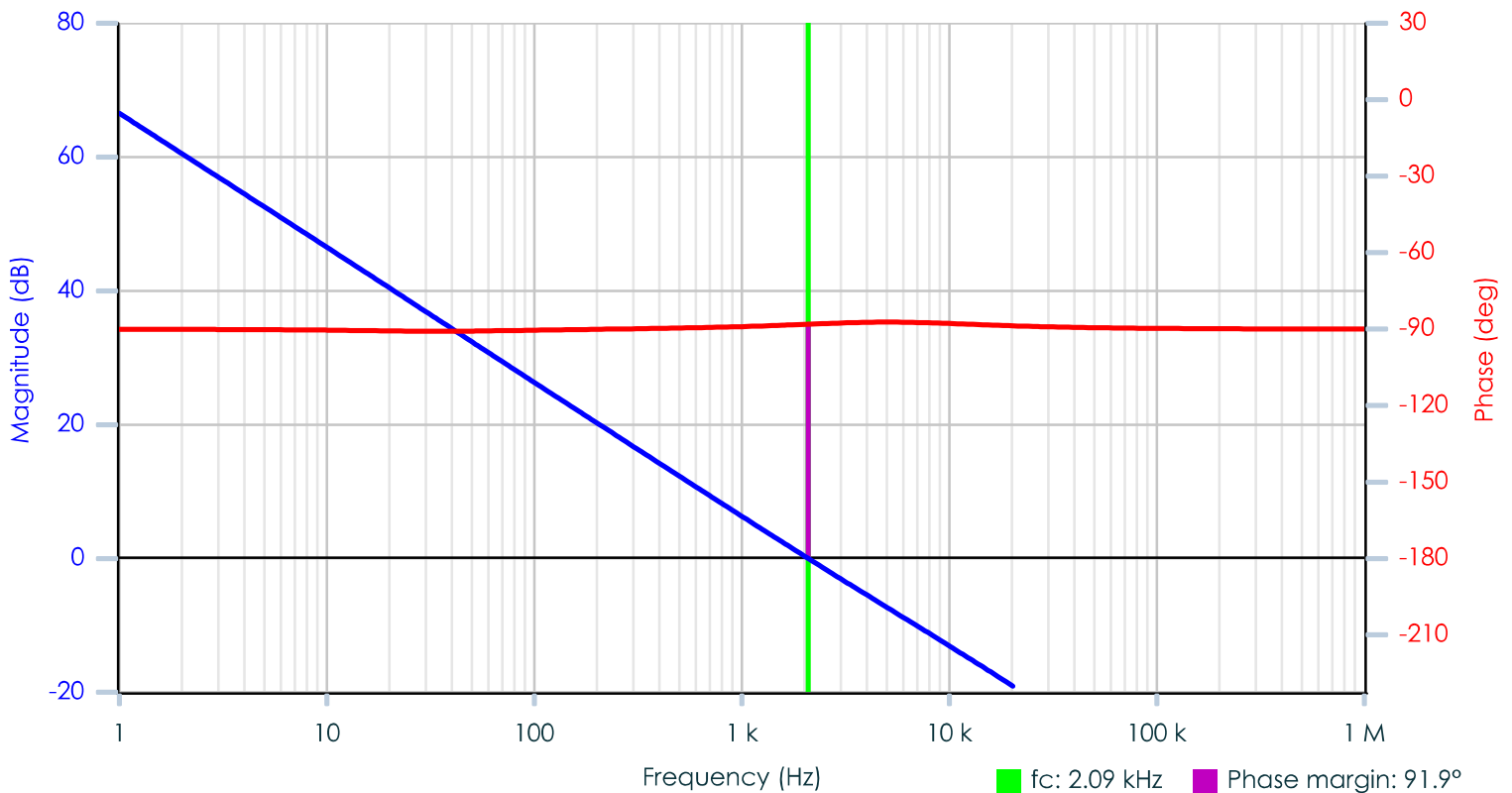
Power losses: 5.89 W - 14.05% details

### Losses Details

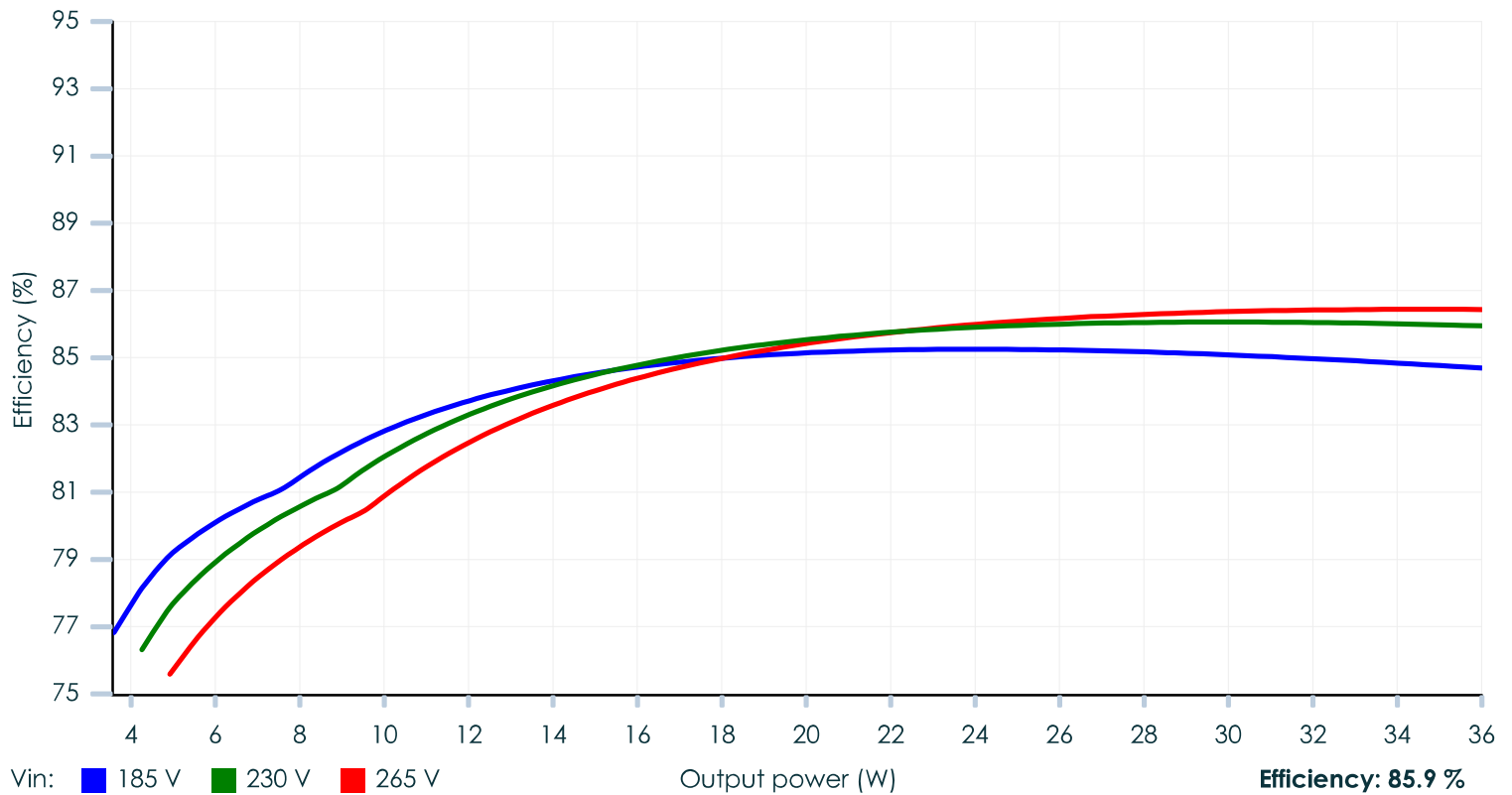


Efficiency: 85.95%

## Bode @ ( Vin 230 Vac - Pout 36 W )



## Efficiency @ ( Vin 230 Vac - Pout 36 W )



## Simulation @ ( Vin 230 Vac - Pout 36 W )

@Vin 185 Vac @Vin 265 Vac @Vin 230 Vac

